

# N-Channel Enhancement-Mode Vertical DMOS FET

#### **Features**

- Free from secondary breakdown
- Low power drive requirement
- Ease of paralleling
- Low C<sub>ISS</sub> and fast switching speeds
- Excellent thermal stability
- Integral source-drain diode
- High input impedance and high gain

#### Applications

- Motor controls
- Converters
- **Amplifiers**
- Switches
- Power supply circuits
- Drivers (relays, hammers, solenoids, lamps, memories, displays, bipolar transistors, etc.)

#### **General Description**

This enhancement-mode (normally-off) transistor utilizes a vertical DMOS structure and Supertex's well-proven, silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally-induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

#### Ordering Information

Part Number	Package Option	Packing		
VN0550N3-G	TO-92	1000/Bag		
VN0550N3-G P002				
VN0550N3-G P003				
VN0550N3-G P005	TO-92	2000/Reel		
VN0550N3-G P013				
VN0550N3-G P014				

<sup>-</sup>G denotes a lead (Pb)-free / RoHS compliant package.

Contact factory for Wafer / Die availablity.

Devices in Wafer / Die form are lead (Pb)-free / RoHS compliant.

## Absolute Maximum Ratings

Parameter	Value
Drain-to-source voltage	BV <sub>DSS</sub>
Drain-to-gate voltage	$BV_{DGS}$
Gate-to-source voltage	±20V
Operating and storage temperature	-55°C to +150°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

## **Typical Thermal Resistance**

Package	$oldsymbol{ heta}_{j_{oldsymbol{a}}}$
TO-92	132°C/W

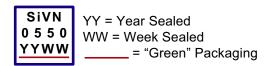
### **Product Summary**

$BV_{DSS}/BV_{DGS}$	R <sub>DS(ON)</sub> (max)	I <sub>DSS</sub> (min)
500V	60Ω	150mA

### **Pin Configuration**

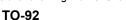


## **Product Marking**



Package may or may not include the following marks: Si or





#### **Thermal Characteristics**

Package	l <sub>D</sub> (continuous) <sup>†</sup>	I <sub>D</sub> (pulsed)	Power Dissipation @T <sub>c</sub> = 25°C	l <sub>DR</sub> †	I <sub>DRM</sub>	
TO-92	50mA	250mA	1.0W	50mA	250mA	

#### Notes:

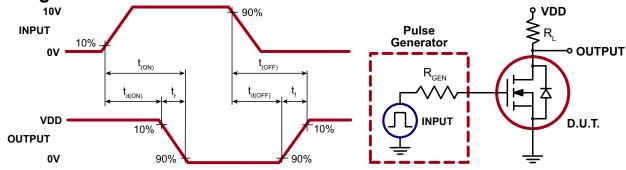
# **Electrical Characteristics** ( $T_A = 25$ °C unless otherwise specified)

Sym	Parameter		Тур	Max	Units	Conditions	
BV <sub>DSS</sub>	Drain-to-source breakdown voltage	500	-	-	V	$V_{GS} = 0V, I_{D} = 1.0 \text{mA}$	
$V_{\rm GS(th)}$	Gate threshold voltage	2.0	-	4.0	V	$V_{GS} = V_{DS}$ , $I_{D} = 1.0 \text{mA}$	
$\Delta V_{GS(th)}$	Change in V <sub>GS(th)</sub> with temperature	_	-3.8	-5.0	mV/°C	$V_{GS} = V_{DS}$ , $I_{D} = 1.0 \text{mA}$	
l <sub>GSS</sub>	Gate body leakage current	-	-	100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
		_	-	10	μA	$V_{GS} = 0V, V_{DS} = Max Rating$	
l <sub>DSS</sub>	Zero gate voltage drain current	-	-	1.0	mA	$V_{DS} = 0.8$ Max Rating, $V_{GS} = 0V$ , $T_{A} = 125^{\circ}C$	
	On state dunin surrent	-	100	-	A	$V_{GS} = 5.0V, V_{DS} = 25V$	
D(ON)	On-state drain current	150	350	_	mA	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 25V	
Б	Static drain-to-source on-state	-	45	-	0	$V_{GS} = 5.0V, I_{D} = 50mA$	
R <sub>DS(ON)</sub>	resistance	-	40	60	Ω	V <sub>GS</sub> = 10V, I <sub>D</sub> = 50mA	
$\Delta R_{DS(ON)}$	Change in R <sub>DS(ON)</sub> with temperature	-	1.0	1.7	%/°C	$V_{GS} = 10V, I_D = 50mA$	
G <sub>FS</sub>	Forward transconductance	50	100	-	mmho	$V_{DS} = 25V, I_{D} = 50mA$	
C <sub>ISS</sub>	Input capacitance	-	45	55		V <sub>GS</sub> = 0V,	
C <sub>oss</sub>	Common source output capacitance	-	8.0	10	pF	$V_{DS} = 25V,$	
C <sub>RSS</sub>	Reverse transfer capacitance	-	2.0	5.0		f = 1.0MHz	
t <sub>d(ON)</sub>	Turn-on time	-	-	10			
t <sub>r</sub>	Rise time	-	-	15	ns	$V_{DD} = 25V,$	
t <sub>d(OFF)</sub>	Turn-off time	-	-	10		$I_D = 150 \text{mA},$ $R_{GEN} = 25 \Omega$	
t <sub>f</sub>	Fall time	-		10		GEN	
$V_{\text{SD}}$	Diode forward voltage drop	-	0.8	-	V	$V_{GS} = 0V, I_{SD} = 500 \text{mA}$	
t <sub>rr</sub>	Reverse recovery time	-	300	-	ns	$V_{GS} = 0V, I_{SD} = 500 \text{mA}$	

#### Notes:

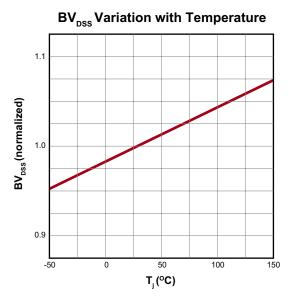
- 1. All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: 300µs pulse, 2% duty cycle.)
- 2. All A.C. parameters sample tested.

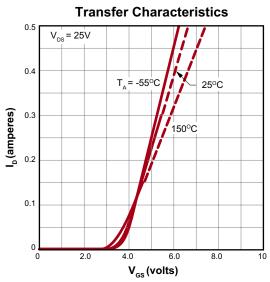
# **Switching Waveforms and Test Circuit**

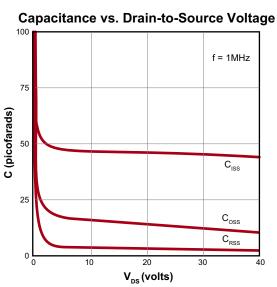


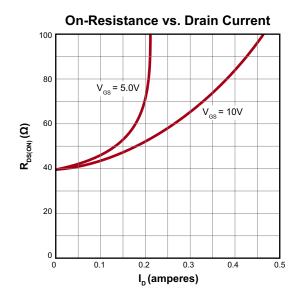
<sup>†</sup>  $I_D$  (continuous) is limited by max rated  $T_i$ .

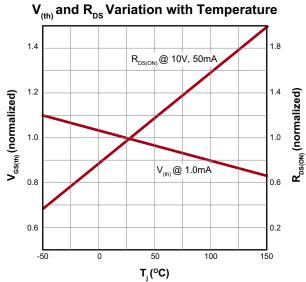
## **Typical Performance Curves**

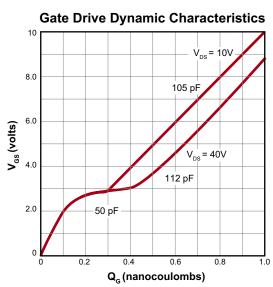




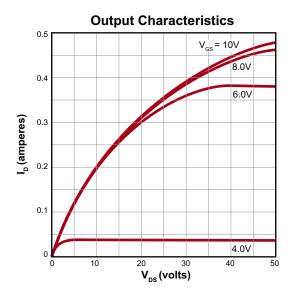


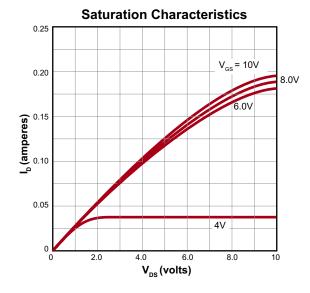


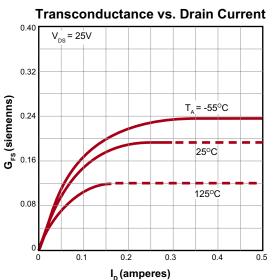


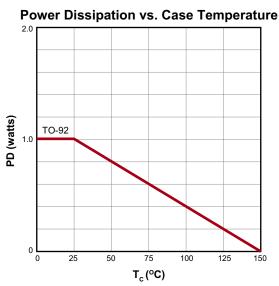


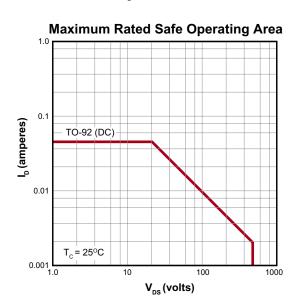
## Typical Performance Curves (cont.)

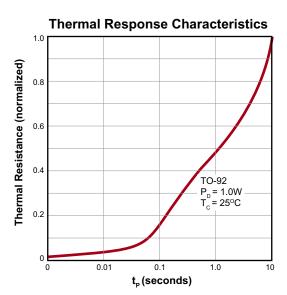




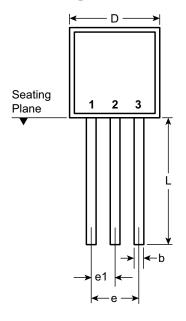


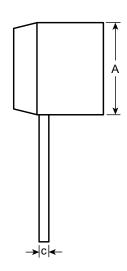






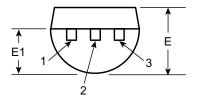
# 3-Lead TO-92 Package Outline (N3)





**Front View** 

**Side View** 



**Bottom View** 

Symb	ol	Α	b	С	D	E	E1	е	e1	L
	MIN	.170	.014 <sup>†</sup>	.014 <sup>†</sup>	.175	.125	.080	.095	.045	.500
Dimensions (inches)	NOM	-	-	-	-	-	-	-	-	-
(51100)	MAX	.210	.022†	.022†	.205	.165	.105	.105	.055	.610*

JEDEC Registration TO-92.

Drawings not to scale.

Supertex Doc.#: DSPD-3TO92N3, Version E041009.

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to <a href="http://www.supertex.com/packaging.html">http://www.supertex.com/packaging.html</a>.)

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<sup>\*</sup> This dimension is not specified in the JEDEC drawing.

<sup>†</sup> This dimension differs from the JEDEC drawing.